

**A METHOD FOR MANUFACTURING A SEMICONDUCTOR
DEVICE HAVING A SILICIDED GATE ELECTRODE AND A METHOD
FOR MANUFACTURING AN INTEGRATED CIRCUIT INCLUDING THE SAME**

ABSTRACT OF THE DISCLOSURE

The present invention provides a method for manufacturing a semiconductor device and a method for manufacturing an integrated circuit including the semiconductor device. The method for manufacturing the semiconductor device (100), among other possible steps, includes forming a polysilicon gate electrode over a substrate (110) and forming source/drain regions (170) in the substrate (110) proximate the polysilicon gate electrode. The method further includes forming a blocking layer (180) over the source/drain regions (170), the blocking layer (180) comprising a metal silicide, and siliciding the polysilicon gate electrode to form a silicided gate electrode (150).